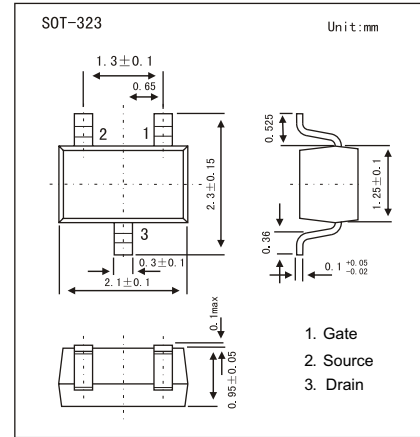


■ Features

- $V_{DS} (V) = 30V$
- $I_D = 0.1 A$
- $R_{DS(ON)} < 8 \Omega$ ($V_{GS} = 4V$)
- $R_{DS(ON)} < 13 \Omega$ ($V_{GS} = 2.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	100	mA
Pulsed Drain Current (Note.1)	I_{DM}	400	
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10\mu s$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250 \mu A$, $V_{GS}=0V$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$, $V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0V$, $V_{GS}=\pm 20V$			± 1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=3V$, $I_D=0.1mA$	0.8		1.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4V$, $I_D=10mA$			8	Ω
		$V_{GS}=2.5V$, $I_D=1mA$			13	
Forward Transconductance	g_{FS}	$V_{DS}=3V$, $I_D=10mA$	20			mS
Input Capacitance	C_{iss}	$V_{GS}=0V$, $V_{DS}=5V$, $f=1MHz$		13		pF
Output Capacitance	C_{oss}			9		
Reverse Transfer Capacitance	C_{rss}			4		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS}=5V$, $V_{DS}=5V$, $I_D=10mA$, $R_L=500 \Omega$, $R_G=10 \Omega$		15		ns
Turn-On Rise Time	t_r			35		
Turn-Off DelayTime	$t_{d(off)}$			80		
Turn-Off Fall Time	t_f			80		

■ Marking

Marking	KN
---------	----

Typical Characteristics

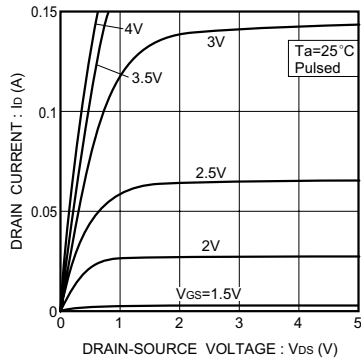


Fig.1 Typical output characteristics

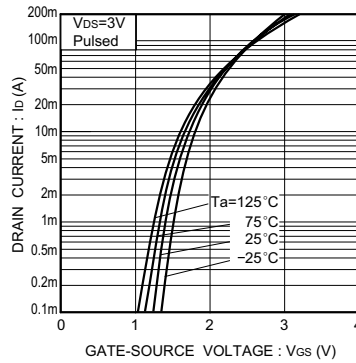


Fig.2 Typical transfer characteristics

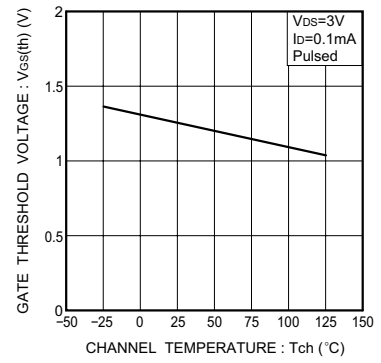


Fig.3 Gate threshold voltage vs. channel temperature

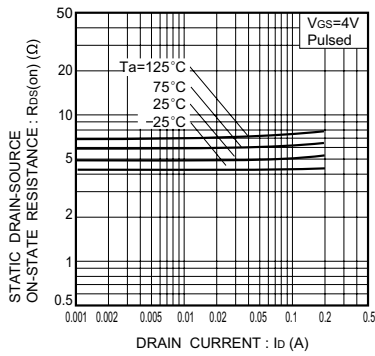


Fig.4 Static drain-source on-state resistance vs. drain current (I)

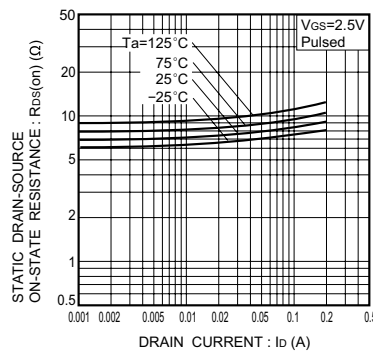


Fig.5 Static drain-source on-state resistance vs. drain current (II)

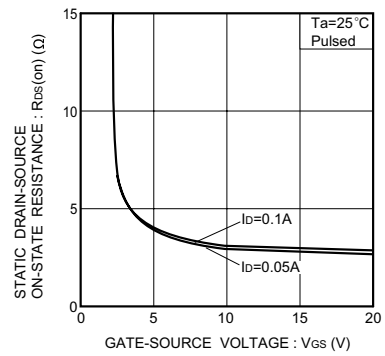


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

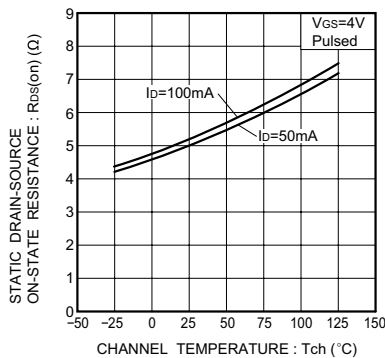


Fig.7 Static drain-source on-state resistance vs. channel temperature

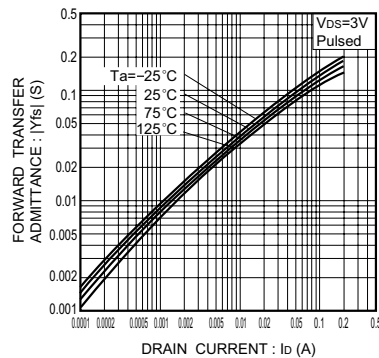


Fig.8 Forward transfer admittance vs. drain current

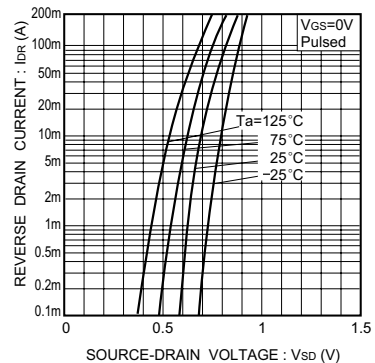


Fig.9 Reverse drain current vs. source-drain voltage (I)

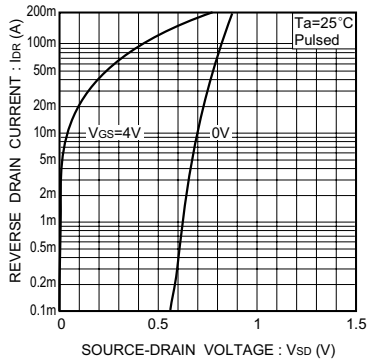
Typical Characteristics


Fig.10 Reverse drain current vs. source-drain voltage (II)

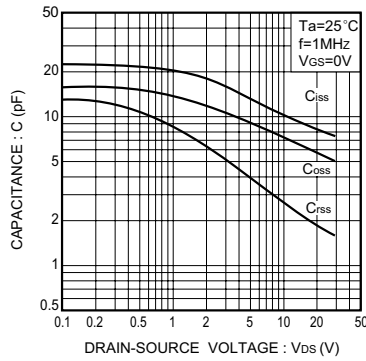


Fig.11 Typical capacitance vs. drain-source voltage

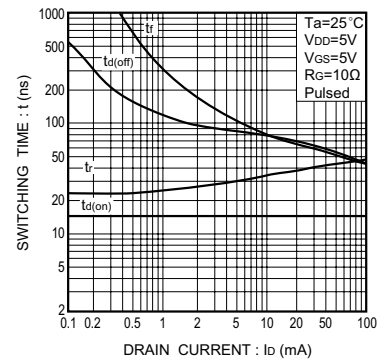
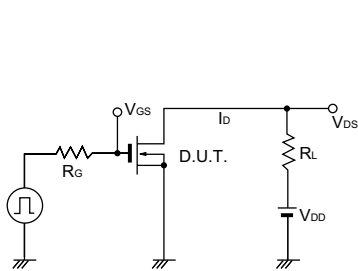

 Fig.12 Switching characteristics
 (See Figures 13 and 14 for the measurement circuit and resultant waveforms)


Fig.13 Switching time measurement circuit

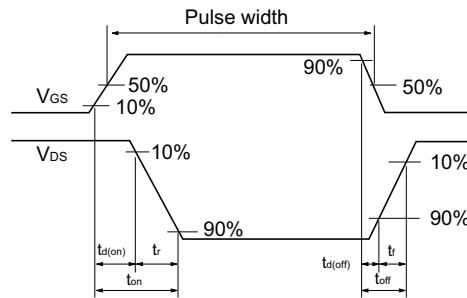


Fig.14 Switching time waveforms

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [LGE](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [FCA20N60_F109](#) [FDZ595PZ](#) [AOD464](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#)
[405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#) [PSMN4R2-30MLD](#)
[TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#)
[NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-](#)
[7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [STU5N65M6](#) [C3M0021120D](#) [DMN13M9UCA6-7](#)
[BSS340NWH6327XTSA1](#) [MCM3400A-TP](#) [DMTH10H4M6SPS-13](#) [IRF40SC240ARMA1](#) [IPS60R1K0PFD7SAKMA1](#)
[IPS60R360PFD7SAKMA1](#) [IPS60R600PFD7SAKMA1](#)